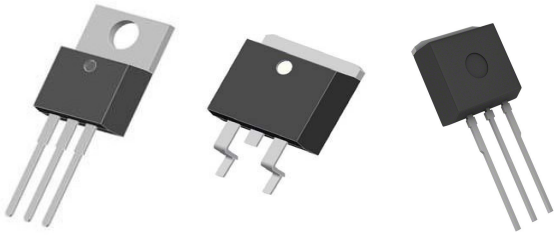
KERSEMI ELECTRONIC CO.,LTD.

IRF640N
IRF640NS
IRF640NL

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Ease of Paralleling
- Simple Drive Requirements

TO-220AB	D^2Pak	TO-262
IRF640N	IRF640NS	IRF640NL

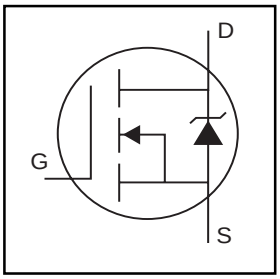


Description

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

The D^2Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D^2Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF640NL) is available for low-profile application.



V_{DSS} = 200V

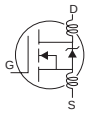
$R_{DS(on)}$ = 0.15Ω

I_D = 18A

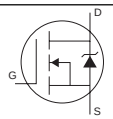
Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	18	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	13	
I_{DM}	Pulsed Drain Current ①	72	
P_D @T_C = 25°C	Power Dissipation	150	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	247	mJ
I_{AR}	Avalanche Current①	18	A
E_{AR}	Repetitive Avalanche Energy①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ⑥	8.1	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew④	10 lbf•in (1.1N•m)	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.25	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.15	Ω	V_{GS} = 10V, I_D = 11A ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	6.8	—	—	S	V_{DS} = 50V, I_D = 11A ③
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V_{DS} = 200V, V_{GS} = 0V
		—	—	250		V_{DS} = 160V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	67	nC	I_D = 11A
Q_{gs}	Gate-to-Source Charge	—	—	11		V_{DS} = 160V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	33		V_{GS} = 10V, See Fig. 6 and 13
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	V_{DD} = 100V
t_r	Rise Time	—	19	—		I_D = 11A
$t_{d(off)}$	Turn-Off Delay Time	—	23	—		R_G = 2.5Ω
t_f	Fall Time	—	5.5	—		R_D = 9.0Ω, See Fig. 10 ③
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1160	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	185	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	53	—		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	18	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)①	—	—	72		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J = 25°C, I_S = 11A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	167	251	ns	T_J = 25°C, I_F = 11A
Q_{rr}	Reverse Recovery Charge	—	929	1394	nC	di/dt = 100A/μs ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ④	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient④	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)⑤	—	40	

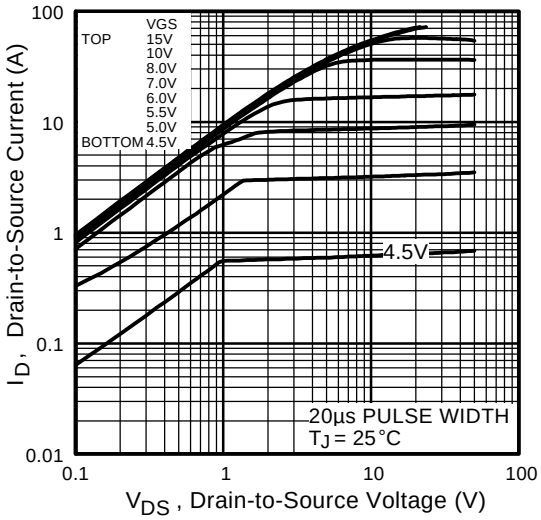


Fig 1. Typical Output Characteristics

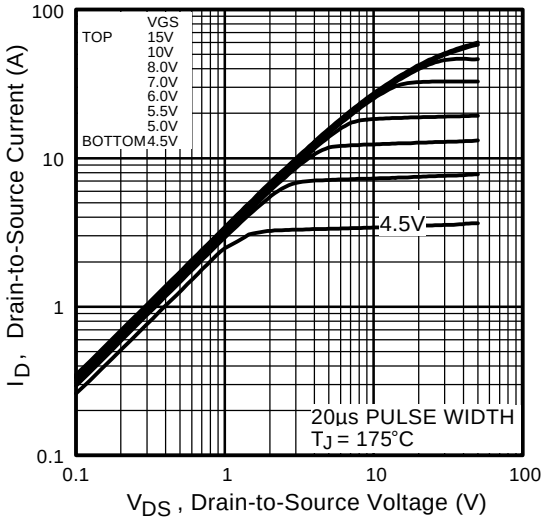


Fig 2. Typical Output Characteristics

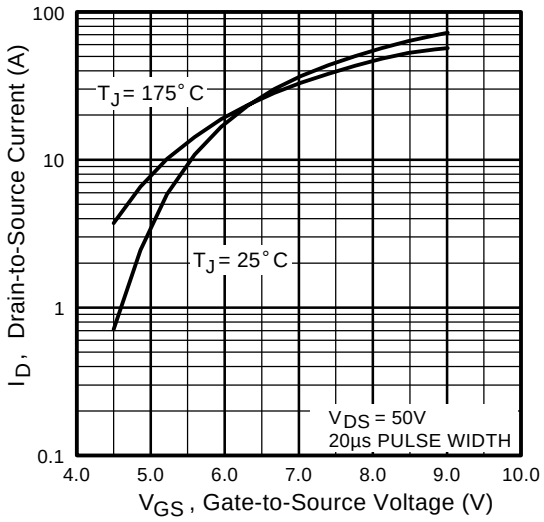


Fig 3. Typical Transfer Characteristics

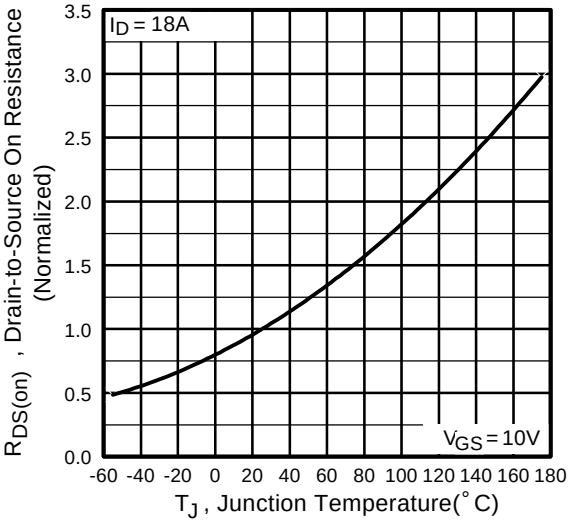


Fig 4. Normalized On-Resistance Vs. Temperature

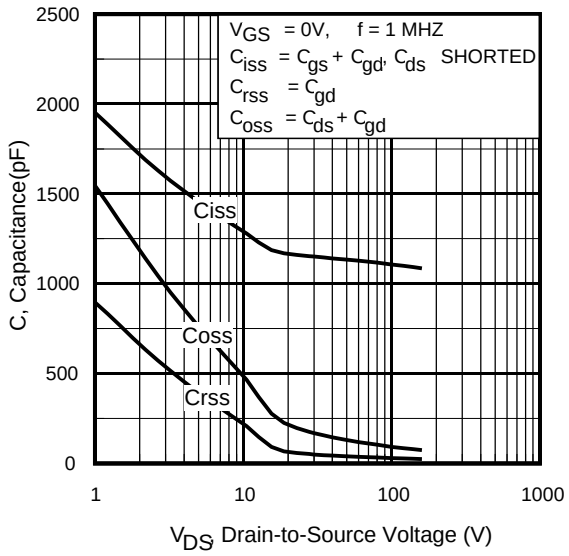


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

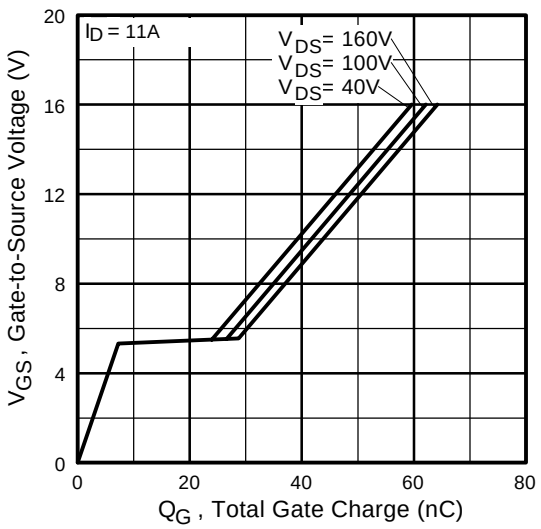


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

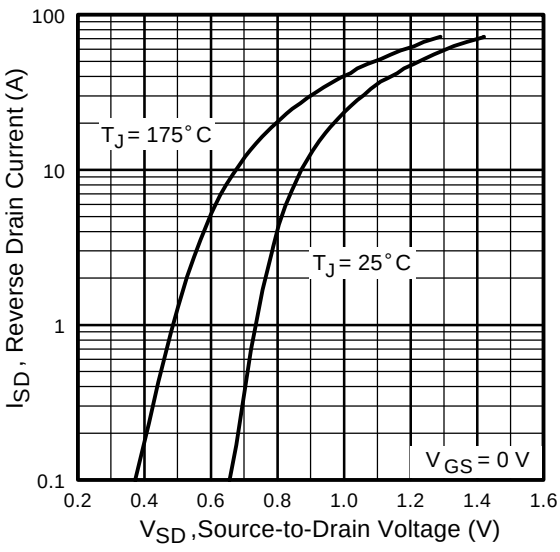


Fig 7. Typical Source-Drain Diode Forward Voltage

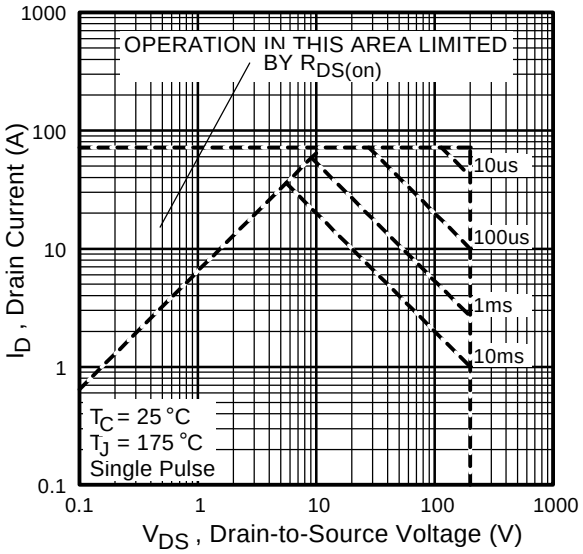


Fig 8. Maximum Safe Operating Area

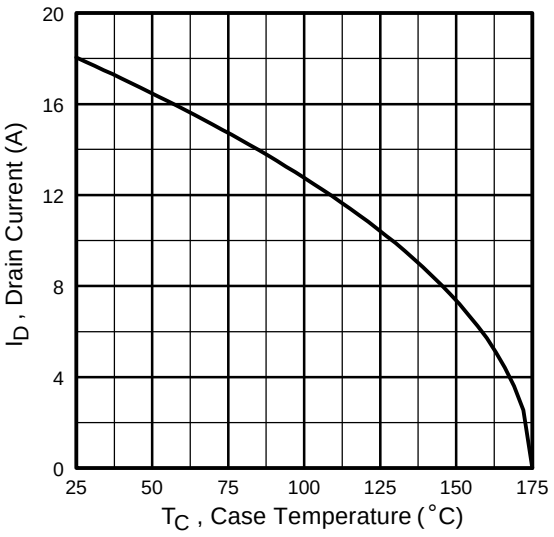


Fig 9. Maximum Drain Current Vs. Case Temperature

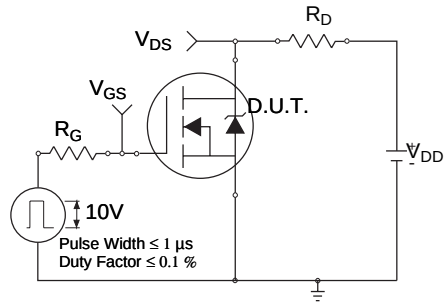


Fig 10a. Switching Time Test Circuit

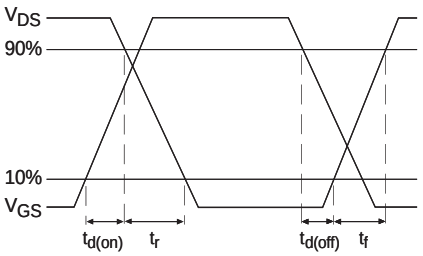


Fig 10b. Switching Time Waveforms

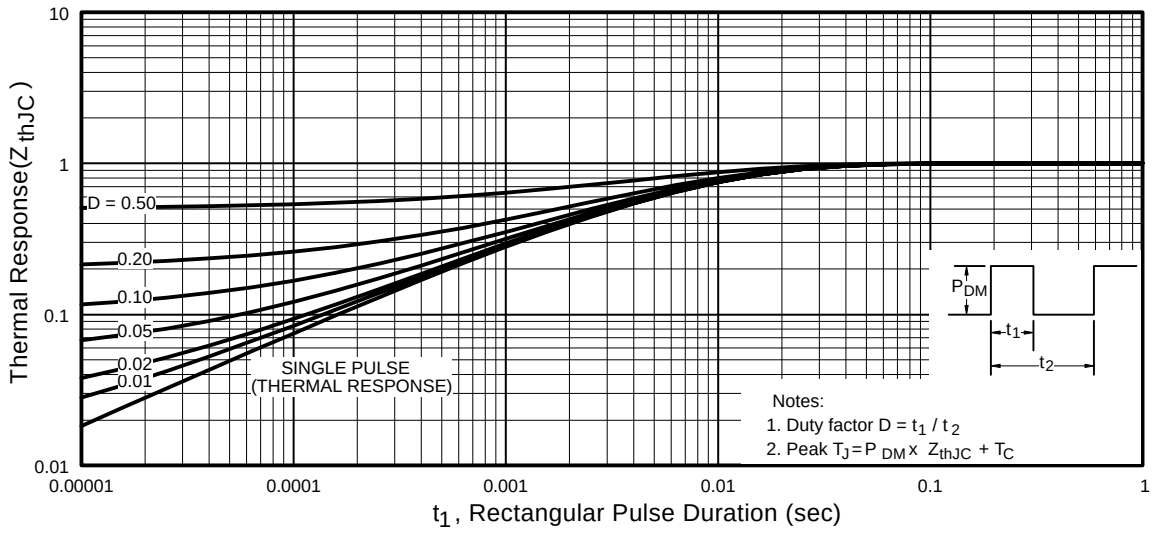


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

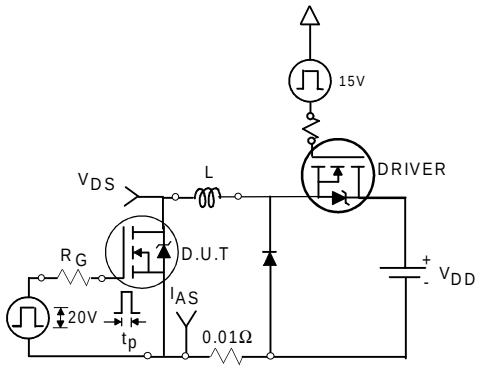


Fig 12a. Unclamped Inductive Test Circuit

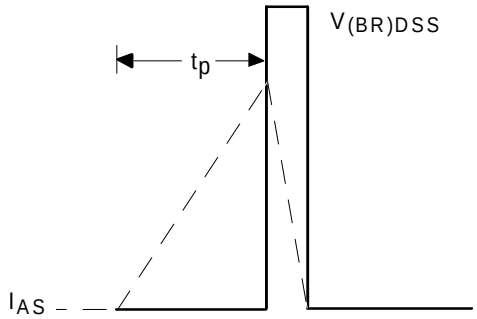


Fig 12b. Unclamped Inductive Waveforms

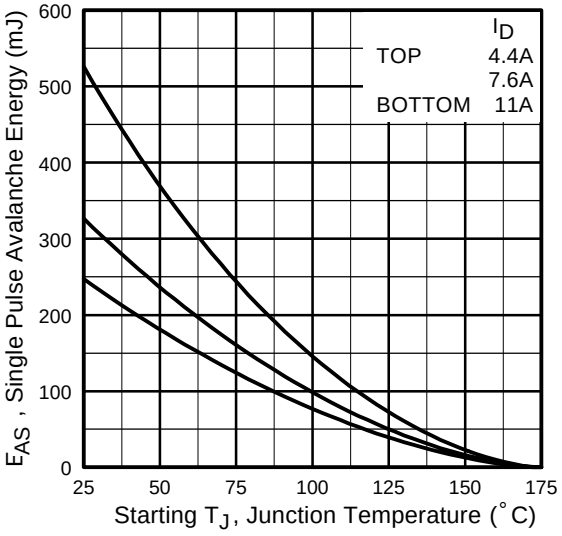


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

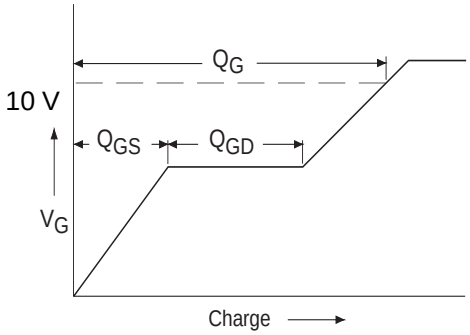


Fig 13a. Basic Gate Charge Waveform

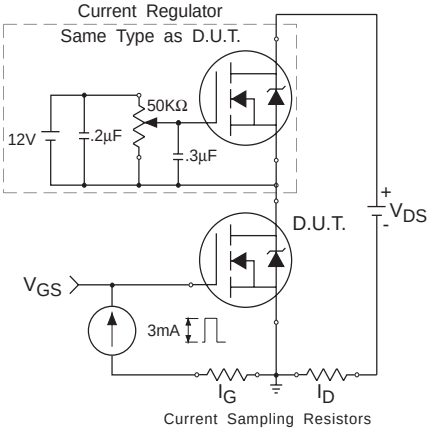
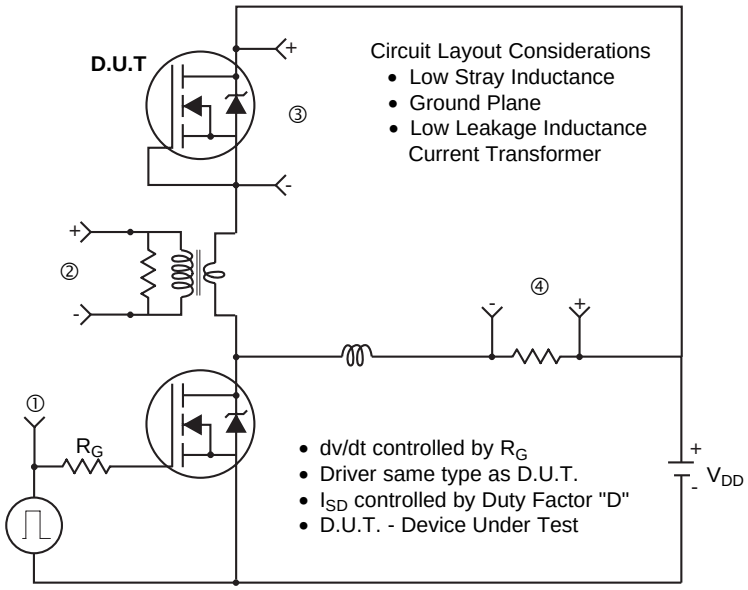
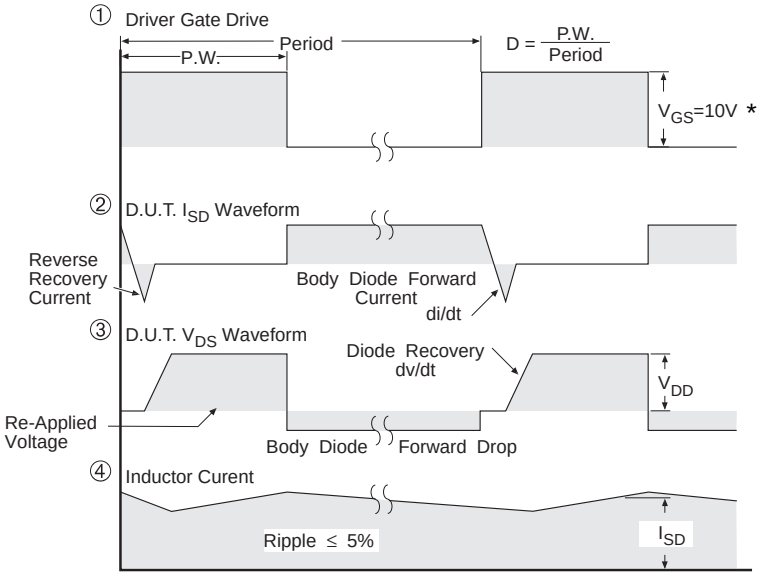


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



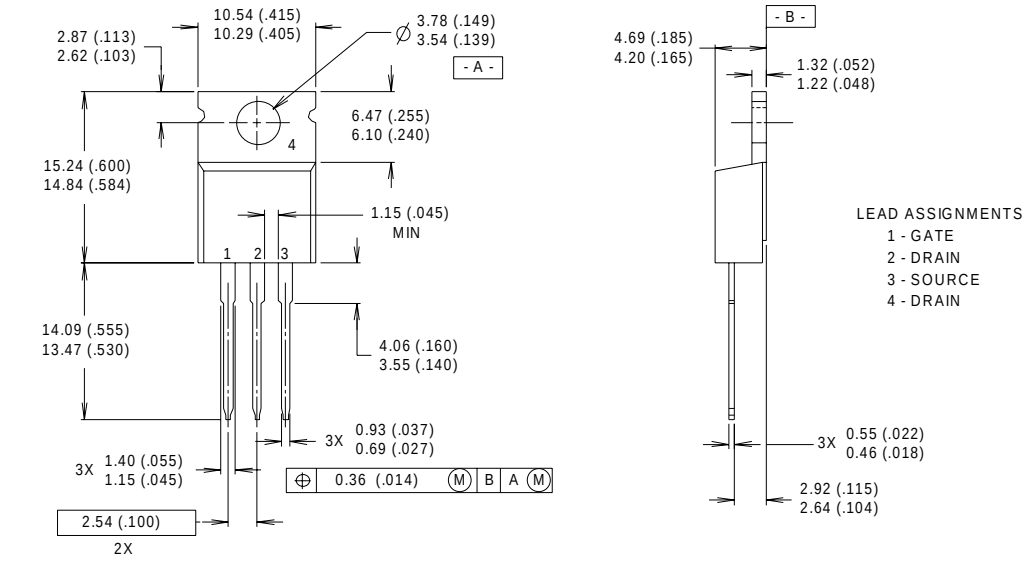


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

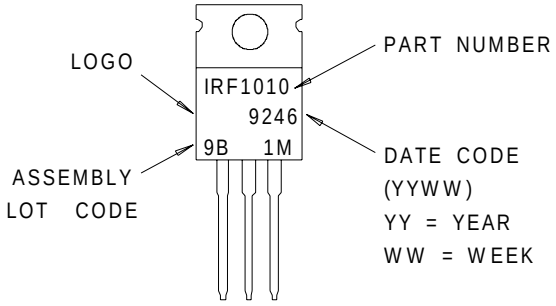


NOTES:

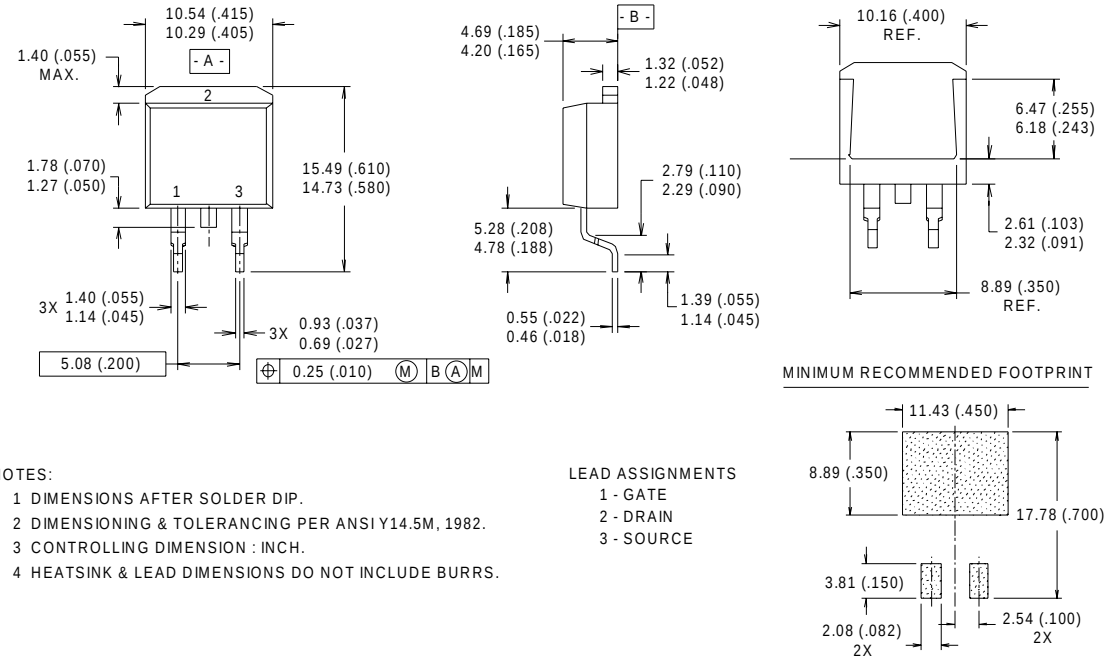
1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
2 CONTROLLING DIMENSION : INCH
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE : THIS IS AN IRF1010
WITH ASSEMBLY
LOT CODE 9B1M



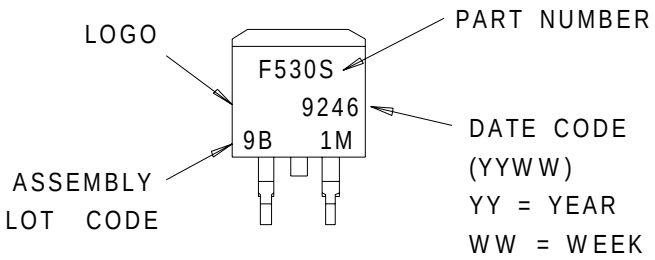
D²Pak Package Outline



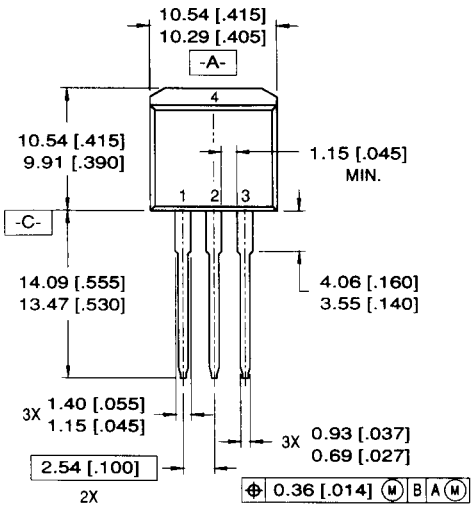
NOTES:
1 DIMENSIONS AFTER SOLDER DIP.
2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
3 CONTROLLING DIMENSION : INCH.
4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS
1 - GATE
2 - DRAIN
3 - SOURCE

D²Pak Part Marking Information



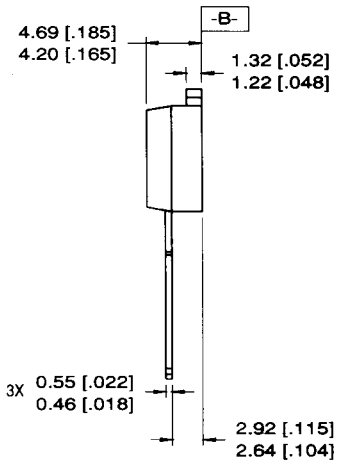
TO-262 Package Outline



LEAD ASSIGNMENTS

1 = GATE 3 = SOURCE

2 = DRAIN 4 = DRAIN



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

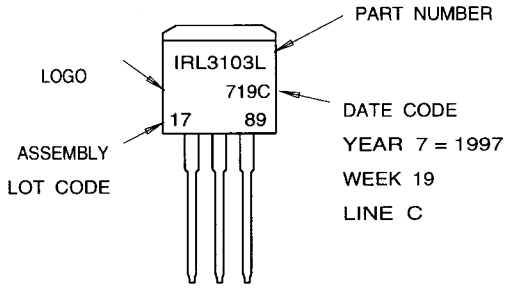
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L

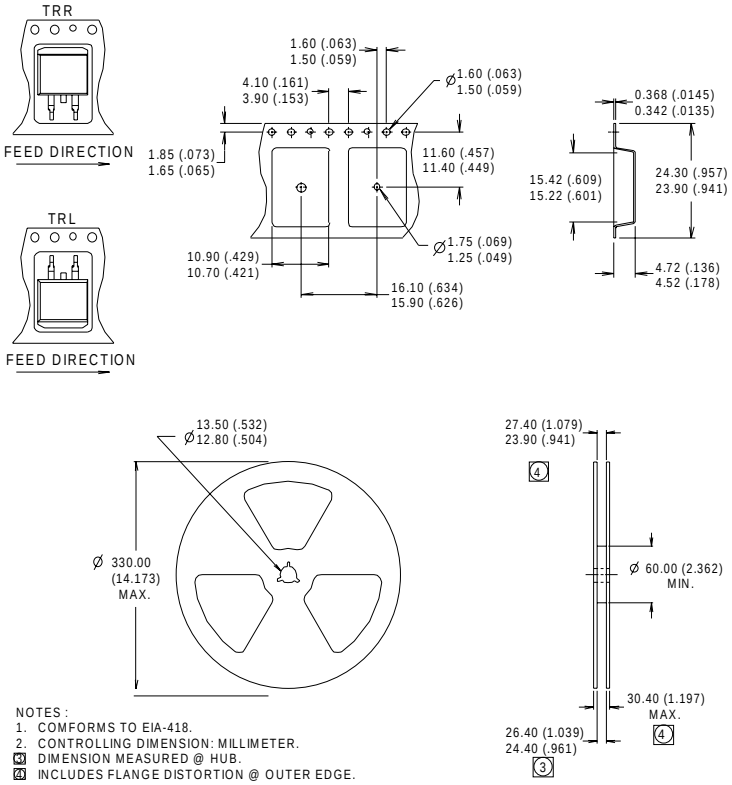
LOT CODE 1789

ASSEMBLED ON WW 19, 1997

IN THE ASSEMBLY LINE "C"



D^{2}Pak Tape & Reel Information



Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 4.2mH
R_G = 25Ω, I_{AS} = 11A.

③ Pulse width ≤ 400μs; duty cycle ≤ 2%.

④ This is only applied to TO-220AB package

⑤ This is applied to D^{2}Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

⑥ I_{SD} ≤ 11A, di/dt ≤ 344A/μs, V_{DD} ≤ $V_{(BR)DSS}$,
T_J ≤ 175°C